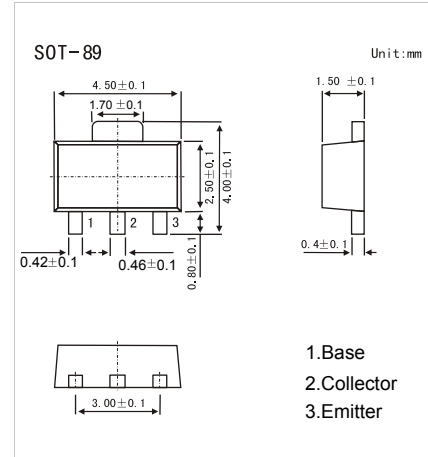


**NPN Transistors**

**2SC2883**

■ Features

- Suitable for output stage of 3 watts amplifier
- Small flat package
- $P_c = 1.0$  to  $2.0$  W (mounted on a ceramic substrate)
- Complementary to 2SA1203



■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	30	V
Collector - Emitter Voltage	$V_{CE0}$	30	
Emitter - Base Voltage	$V_{EB0}$	5	
Collector Current - Continuous	$I_C$	1.5	A
Base Current	$I_B$	0.3	
Collector Power Dissipation (Note.1)	$P_C$	500 1000	mW
Junction Temperature	$T_J$	150	
Storage Temperature Range	$T_{stg}$	-55 to 150	

Note.1: Mounted on a ceramic substrate ( $250\text{ mm}^2 \times 0.8\text{ t}$ )

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_C = 1\text{mA}, I_E = 0$	30			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_C = 10\text{mA}, I_B = 0$	30			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = 1\text{mA}, I_C = 0$	5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = 30\text{V}, I_E = 0$			0.1	uA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5\text{V}, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1.5\text{A}, I_B = 30\text{mA}$			2	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 1.5\text{A}, I_B = 30\text{mA}$			1.2	
Base - emitter voltage	$V_{BE}$	$V_{CE} = 2\text{V}, I_C = 500\text{mA}$			1	
DC current gain	$h_{FE}$	$V_{CE} = 2\text{V}, I_C = 500\text{mA}$	100		320	
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$			40	pF
Transition frequency	$f_T$	$V_{CE} = 2\text{V}, I_C = 500\text{mA}$		120		MHz

■ Classification of  $h_{FE}$

Marking	GO*	GY*
Rank	O	Y
Range	100-200	160-320



炬芯微  
XUANXINWEI

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Typical Characteristics

